

**PATENT NUMBER**

**O.I.P.E.**

**PATENT DATE**

SCANNED 93 Q.A.

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Method for manufacturing a high voltage MOSFET semiconductor device with enhanced charge controllability

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<input type="checkbox"/> <b>TERMINAL DISCLAIMER</b>	<b>DRAWINGS</b> Sheets Drwg.      Figs. Drwg.      Print Fig.		<b>CLAIMS ALLOWED</b> Total Claims      Print Claim for O.G.	
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<input type="checkbox"/> The term of this patent shall not extend beyond the expiration date of U.S. Patent, No. _____	_____ (Assistant Examiner)      (Date)		<b>ISSUE FEE</b>	
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